

ABSTRACT

A pattern forming method comprising a step of applying a resist composition whose solubility in a negative tone developer decreases upon irradiation with an actinic ray or radiation and which contains a resin having an alicyclic hydrocarbon structure and a dispersity of 1.7 or less and being capable of increasing the polarity by the action of an acid, an exposure step, and a development step using a negative tone developer; a resist composition for use in the method; and a developer and a rinsing solution for use in the method, are provided, whereby a pattern with reduced line edge roughness and high dimensional uniformity can be formed.